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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/092,525	03/08/2002	Keishiro Okamoto	020214	3829
38834	7590	12/05/2005	EXAMINER	
WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP			GEBREMARIAM, SAMUEL A	
1250 CONNECTICUT AVENUE, NW			ART UNIT	PAPER NUMBER
SUITE 700				2811
WASHINGTON, DC 20036				

DATE MAILED: 12/05/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)
	10/092,525	OKAMOTO ET AL. <i>(AN)</i>
	Examiner	Art Unit
	Samuel A. Gebremariam	2811

— The MAILING DATE of this communication appears on the cover sheet with the correspondence address —
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
 - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
 - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on 19 September 2005.
- 2a) This action is FINAL. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) Claim(s) 1,2 and 4-20 is/are pending in the application.
- 4a) Of the above claim(s) 15-20 is/are withdrawn from consideration.
- 5) Claim(s) _____ is/are allowed.
- 6) Claim(s) 1,2 and 4-14 is/are rejected.
- 7) Claim(s) _____ is/are objected to.
- 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) Notice of References Cited (PTO-892)
- 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____.
- 4) Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) Notice of Informal Patent Application (PTO-152)
- 6) Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

2. Claim 1 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. It is unclear which element forms wires of second uniform pitch as recited in the claim.

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claims 1-2, 4-6, 8-10 and 13-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chakravorty, US patent No. 6,611,419 in view of Gnadinger, US patent No. 5,229,647.

Regarding claim 1, Chakravorty teaches (figs. 2 and 3) a semiconductor apparatus, comprising: a support substrate (310) having through holes filled with conductor (323) in conformity with a first uniform pitch, capacitors (330) formed on the support substrate (310) comprising a lower electrode (329) having a first wide area

(region where lower electrode is formed) and a first cut-away portion (refer to fig. 3, the cut-away portions are the regions where the through holes go through), a dielectric film (340) covering the first wide area (refer to fig. 3) and an upper electrode (326) having a second wide area (region where 326 is formed) and a second cut-away portion (region where through hole goes through adjacent the capacitor region) the first and second wide areas facing via the dielectric film (34) to establish a capacitance (330), wiring layer (322) formed on the support substrate, leading some of the through holes filled with conductor upwards via the capacitor (330), having branches (bent portion of 322), above the upper electrode (326) to form wires (301) of second uniform pitch narrower than the first uniform pitch (refer to col. 4, lines 42-51, where it is stated that the signal wires 223/323 are shown to be wider than the die bump (201/301) pitch) and plural semiconductor elements (IC die 300) disposed on the wiring layer (322), having terminals (IC die inherently has terminals) in conformity with the second uniform-pitch, and connected with the wiring layer via the terminals (refer to fig. 3).

Chakravorty does not teach a support substrate made of a semiconductor substrate. However Chakravorty teaches (col. 4, lines 23-25) that die 200/300 and substrate 210/310 can be of any type.

Gnadinger teaches (fig. 4, col. 3, lines 37-57) the use of a semiconductor wafer (10) as a support in the structure of forming an interconnect structure.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the semiconductor substrate taught by Gnadinger in the structure of Chakravorty in order to form a high density interconnection structure.

Regarding claim 2, Chakravorty teaches substantially the entire claimed structure of claim 1 above including a circuit board (320, col. 4, lines 59-67) having wiring of a first uniform pitch and connected to lower surfaces of the through holes (323) fills with conductor.

Regarding claims 4 and 5, Chakravorty teaches (fig. 3) substantially the entire claimed structure of claim 1 above including the support substrate is a Si substrate (10) having through holes (refer to fig. 3 of Gnadinger) with an insulation film (24) formed on the side walls of the holes, and the through holes filled with conductor are metallic conductors packed in the through holes.

Regarding claim 6, Chakravorty teaches substantially (figs. 4 of Gnadinger, col. 3, lines 37-57) the entire claimed structure of claim 1 above including the insulation film is a silicon oxide film (24) and lower surfaces of the silicon substrate are also covered with an insulating material (27).

The limitation that the silicon oxide film is formed by thermal oxidation is not given patentable weight because, this is considered a product-by-process claim. “[E]ven though product-by process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process.” *In re Thorpe*, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985).

Regarding claims 8 and 9, Chakravorty teaches substantially the entire claimed structure of claim 1 above including the through holes filled with conductor (fig. 3) include a first signal wire the wiring layer contains a second signal wire (323) for leading the first signal wire substantially vertically; and the capacitor has electrodes (326 and 329) with a vacancy (region between the electrodes) around a region where the second signal wire is located.

Regarding claim 10, Chakravorty teaches (fig. 3) substantially the entire claimed structure of claim 1 above except explicitly stating that the insulation layer disposed on the support substrate, have a thermal expansion coefficient of 10 ppm/ $^{\circ}$ C or less in the in-plane direction, and insulates the wiring layer and the capacitor.

Parameters such as coefficient of thermal expansion and heat capacity in the art of semiconductor manufacturing process are subject to routine experimentation and optimization to achieve the desired device characteristics during fabrication.

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust the thermal expansion coefficient of Chakravorty structure as claimed in order to improve the thermal property of the device.

Regarding claim 13, Chakravorty teaches (fig. 3) substantially the entire claimed structure of claim 1 above including the wiring layer (321) contains a wiring connecting the plural semiconductor elements with each other (die 300 appears to be connected to each other).

Regarding claim 14, Chakravorty teaches (fig. 3) substantially the entire claimed structure of claim 1 above including another circuit part (320) connected with the wiring layer (322) via (331).

5. Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Chakravorty, Gnadinger and in view of Kabumoto et al., US patent No. 5,883,428.

Regarding claim 7, Chakravorty teaches (fig. 1) substantially the entire claimed structure of claim 1 above except explicitly teaching that the capacitor is a decoupling capacitor connected between power wires.

Decoupling capacitors are conventional in the art and are also taught by Kabumoto (fig. 1) for reducing power-supply noise (col. 5, lines 23-48).

Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the decoupling capacitors taught by Kabumoto in the structure of Chakravorty in order to reduce noise between the power wires of Yamauchi's integrated device.

6. Claims 11 and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chakravorty, Gnadinger and in view of Cuchiaro et al. US patent No. 5,888,585.

Regarding claims 11 and 12, Chakravorty teaches substantially the entire claimed structure of claim 1 above except explicitly stating that the capacitor has a capacitor dielectric layer made of an oxide containing at least one of Ba, Sr and Ti, and a pair of capacitor electrodes sandwiching the capacitor dielectric layer and containing at least partially one of Pt, Ir, Ru, Pd or any of their oxides.

Cuchiaro teaches a charge storage device including high dielectric material comprising barium and platinum electrode in the process of making an integrated device.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to form the capacitor structure of Chakravorty device using the materials taught by Cuchiaro in order to form a capacitor structure that is smaller in size and with less leakage current.

Response to Arguments

7. Applicant's arguments with respect to claims 1-14 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

8. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of

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the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Samuel Admassu Gebremariam whose telephone number is (571)-272-1653. The examiner can normally be reached on 8:00am-4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie Lee can be reached on (571) 272-17321732. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Samuel Admassu Gebremariam

November 28, 2005



EDDIE LEE
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800